

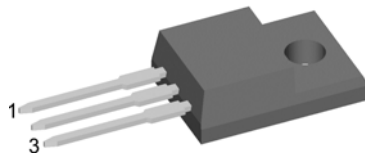
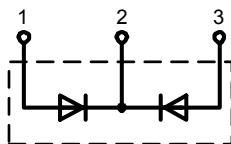
HiPerFRED

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

$$\begin{aligned} V_{RRM} &= 300 \text{ V} \\ I_{FAV} &= 2 \times 10 \text{ A} \\ t_{rr} &= 35 \text{ ns} \end{aligned}$$

Part number (Marking on product)

DPG 20 C 300PN



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{RM} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

- TO-220FPAB
- Industry standard outline
- Plastic overmolded tab for electrical isolation
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

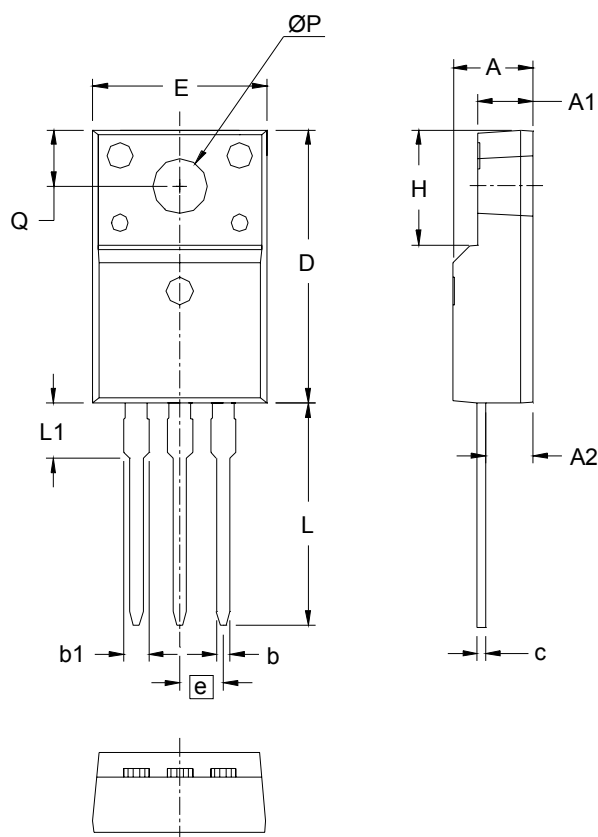
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^\circ\text{C}$			300	V
I_R	reverse current	$V_R = 300 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$			1	μA
		$V_R = 300 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$			0.06	mA
V_F	forward voltage	$I_F = 10 \text{ A}$ $T_{VJ} = 25^\circ\text{C}$			1.27	V
		$I_F = 20 \text{ A}$			1.45	V
		$I_F = 10 \text{ A}$ $T_{VJ} = 150^\circ\text{C}$			0.98	V
		$I_F = 20 \text{ A}$			1.17	V
I_{FAV}	average forward current	rectangular, $d = 0.5$ $T_C = 125^\circ\text{C}$			10	A
V_{F0}	threshold voltage	} for power loss calculation only $T_{VJ} = 175^\circ\text{C}$			0.69	V
r_F	slope resistance				22.8	m Ω
R_{thJC}	thermal resistance junction to case				4.40	K/W
T_{VJ}	virtual junction temperature		-55		175	$^\circ\text{C}$
P_{tot}	total power dissipation	$T_C = 25^\circ\text{C}$			65	W
I_{FSM}	max. forward surge current	$t_p = 10 \text{ ms (50 Hz), sine}$ $T_{VJ} = 45^\circ\text{C}$			100	A
I_{RM}	max. reverse recovery current	$I_F = 10 \text{ A};$ $T_{VJ} = 25^\circ\text{C}$		3		A
		$-di_F/dt = 200 \text{ A}/\mu\text{s}$ $T_{VJ} = 125^\circ\text{C}$				A
t_{rr}	reverse recovery time	$V_R = 100 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$		35		ns
		$T_{VJ} = 125^\circ\text{C}$				ns
C_j	junction capacitance	$V_R = 150 \text{ V}; f = 1 \text{ MHz}$ $T_{VJ} = 25^\circ\text{C}$				pF
E_{AS}	non-repetitive avalanche energy	$I_{AS} = \text{A}; L = \mu\text{H}$ $T_{VJ} = 25^\circ\text{C}$			tbd	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R \text{ typ.}; f = 10 \text{ kHz}$			tbd	A

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin*			35	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
M_D	mounting torque		0.4		0.6	Nm
F_c	mounting force with clip		20		60	N
T_{stg}	storage temperature		-55		150	°C
Weight				2		g

* I_{rms} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-220FPAB



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40